

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	Package	I <sub>D</sub> T <sub>A</sub> = +25°C
-20V	0.9Ω @ V <sub>GS</sub> = -4.5V	SOT23	-430mA
	2.0Ω @ V <sub>GS</sub> = -1.8V		-150mA

## Description

This new generation MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

- DC-DC Converters
- Power Management Functions

## Features

- Low On-Resistance
- Very Low Gate Threshold Voltage V<sub>GS(TH)</sub> <1V
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Gate
- Qualified to AEC-Q101 standards for High Reliability
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

## Mechanical Data

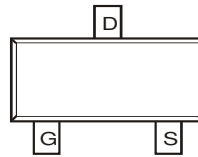
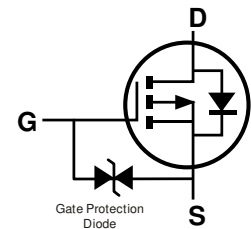
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 **(e3)**
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)



SOT23



Top View


 Top View  
Internal Schematic


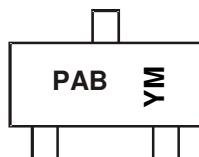
Equivalent Circuit

## Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
DMP2004K-7	Standard	SOT23	3,000/Tape & Reel
DMP2004KQ-7	Automotive	SOT23	3,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



PAB = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: F = 2018)  
 M = Month (ex: 9 = September)

### Date Code Key

Year	2008	2009	~	2018	2019	2020	2021	2022
Code	V	W	~	F	G	H	I	J

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	-20	V
Gate-Source Voltage	V <sub>GSS</sub>	±8	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = -4.5V	I <sub>D</sub>	-600	mA
Pulsed Drain Current	I <sub>DM</sub>	-1.9	A

**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P <sub>D</sub>	550	mW
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	227	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 6)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	-1	μA	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±1.0	μA	V <sub>GS</sub> = ±4.5V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 6)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.5	—	-1.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	0.7	0.9	Ω	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -430mA
		—	1.1	1.4		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -300mA
		—	1.7	2.0		V <sub>GS</sub> = -1.8V, I <sub>D</sub> = -150mA
Forward Transfer Admittance	Y <sub>fs</sub>	200	—	—	ms	V <sub>DS</sub> = -10V, I <sub>D</sub> = -0.2A
Diode Forward Voltage (Note 6)	V <sub>SD</sub>	-0.5	—	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -115mA
<b>DYNAMIC CHARACTERISTICS (Note 7)</b>						
Input Capacitance	C <sub>ISS</sub>	—	—	175	pF	V <sub>DS</sub> = -16V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>OSS</sub>	—	—	30	pF	
Reverse Transfer Capacitance	C <sub>RSS</sub>	—	—	20	pF	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	8.5	—	ns	V <sub>DD</sub> = -3V, V <sub>GS</sub> = -2.5V, R <sub>L</sub> = 300Ω, R <sub>g</sub> = 25Ω, I <sub>D</sub> = -100mA
Turn-On Rise Time	t <sub>R</sub>	—	4.3	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	20.2	—	ns	
Turn-Off Fall Time	t <sub>F</sub>	—	19.2	—	ns	

- Notes:
5. Device mounted on FR-4 PCB.
  6. Short duration pulse test used to minimize self-heating effect.
  7. Guaranteed by design. Not subject to product testing.

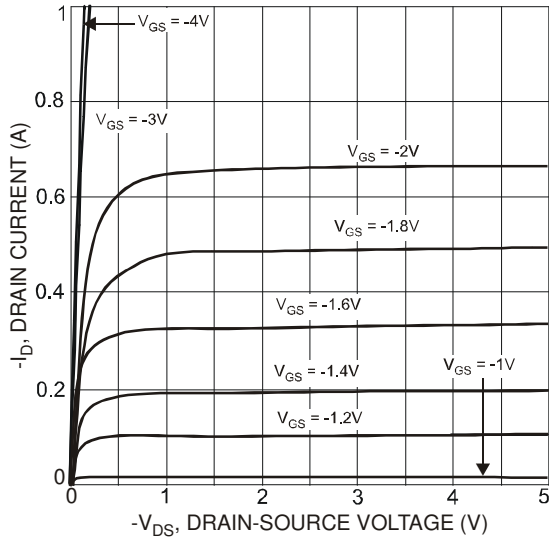


Figure 1 Typical Output Characteristics

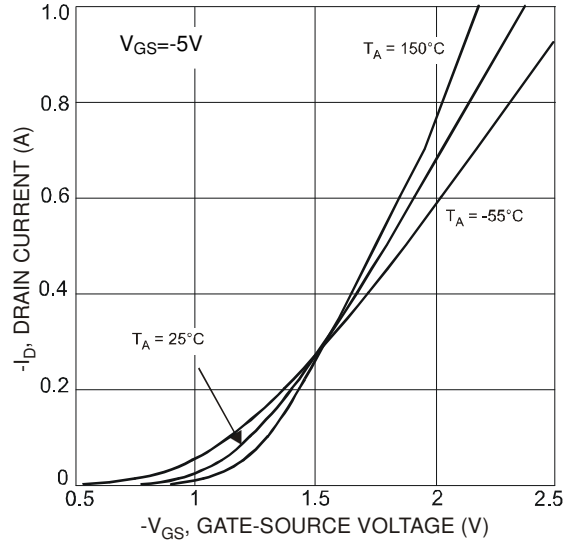


Figure 2 Typical Transfer Characteristics

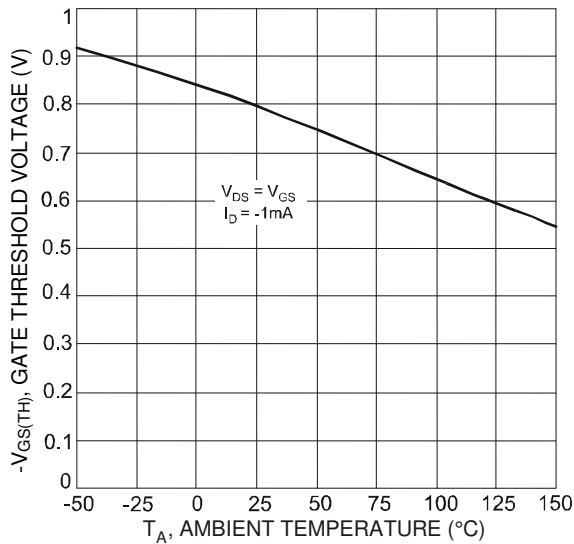


Figure 3 Gate Threshold Voltage vs. Ambient Temperature

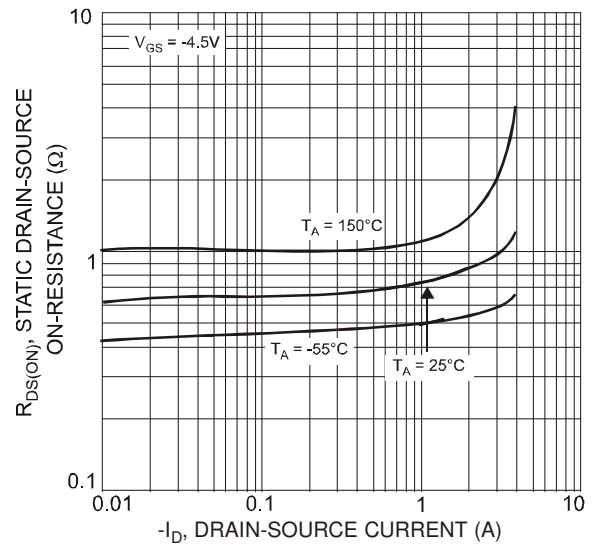


Figure 4 Static Drain-Source On-Resistance vs. Drain Current

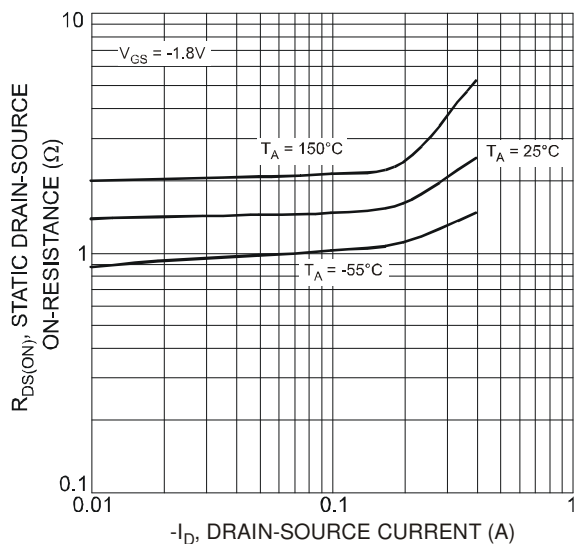


Figure 5 Static Drain-Source On-Resistance vs. Drain Current

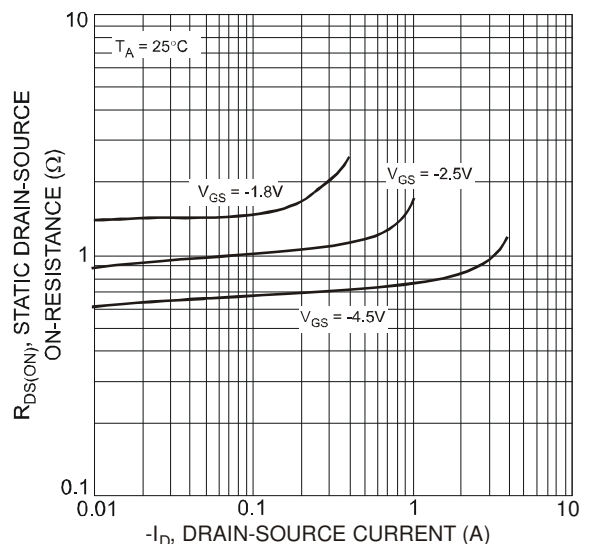


Figure 6 Static Drain-Source On-Resistance vs. Drain-Source Current

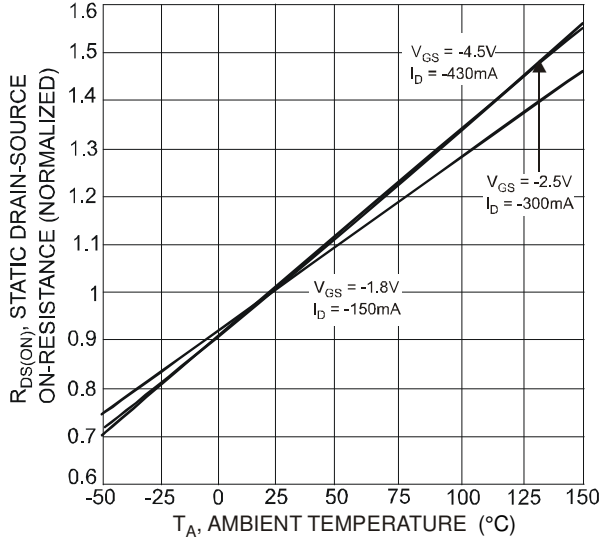


Figure 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

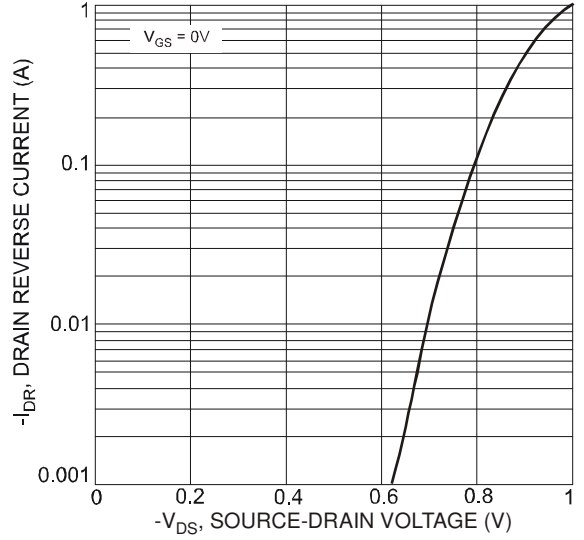


Figure 8 Reverse Drain Current vs. Source-Drain Voltage

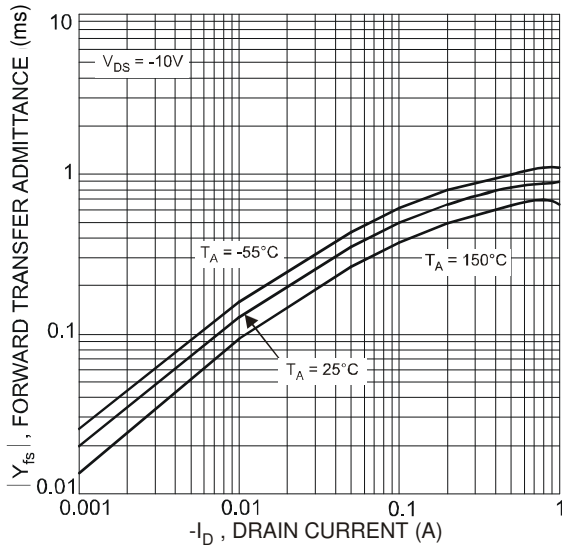


Figure 9 Forward Transfer Admittance vs. Drain Current

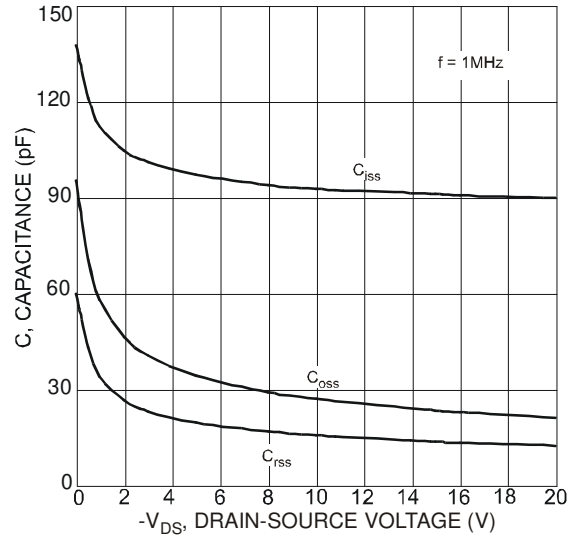
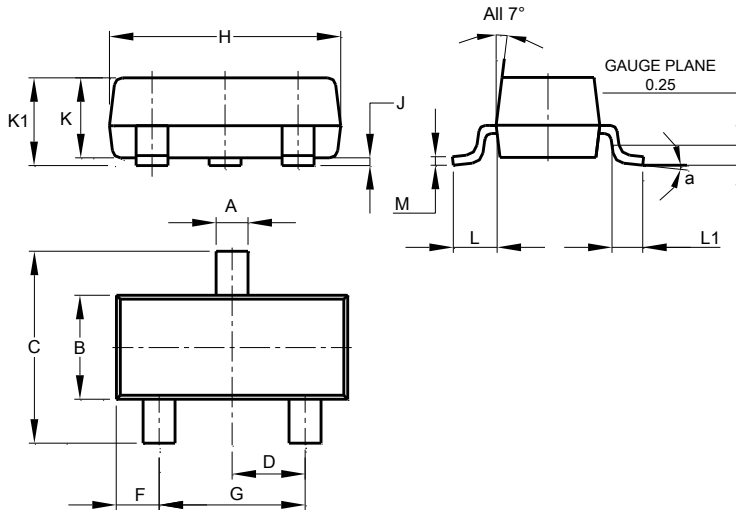


Figure 10 Typical Capacitance

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT23**

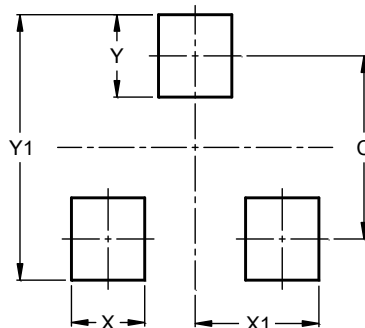


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
<b>All Dimensions in mm</b>			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT23**



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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